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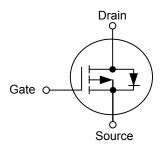
### **Power MOSFET**

# P-CHANNEL ENHANCEMENT MODE

### DESCRIPTION

The UTC **UT9435H** provide excellent  $R_{DS(ON)}$ , low gate charge and fast switching speed. It has been optimized for power management applications.

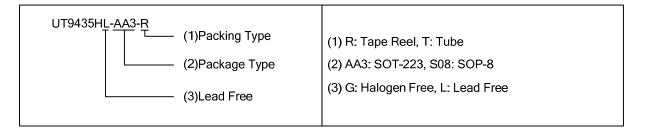
### SYMBOL



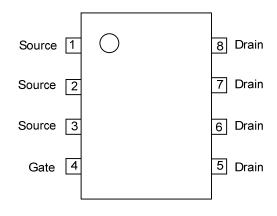
# SOP-8

### ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment						Decking		
Lead Free	Halogen Free	Package	1	2	З	4	5	6	7	8	Packing
UT9435HL-AA3-R	UT9435HG-AA3-R	SOT-223	G	D	S	I	I	I	1	I	Tape Reel
UT9435HL-S08-R	UT9435HG-S08-R	SOP-8	ഗ	ഗ	ഗ	G	D	D	D	D	Tape Reel
UT9435HL-S08-T	UT9435HG-S08-T	SOP-8	S	S	S	G	D	D	D	D	Tube



### ■ PIN CONFIGURATION





### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current (Note 3)	T <sub>A</sub> =125℃	I <sub>D</sub>	±5.3	Α
Pulsed Drain Current (Note 1, 2)		I <sub>DM</sub>	±20	Α
Power Dissipation		PD	2.5	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	$\theta_{JA}$	50	°C <b>/W</b>

### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub> =25°C, unless otherwise specified)

	i	1	+						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =-250 μA	-30			V			
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24 V, V <sub>GS</sub> =0 V			-1	μA			
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0 V, V <sub>GS</sub> = ±20V			±100	nA			
ON CHARACTERISTICS									
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250 μA	-1		-3	V			
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.3A		44	50	mΩ			
Drain-Source On-State Resistance (Note 2)		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A		74	90	mΩ			
On State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> =-10V	-20			А			
DYNAMIC PARAMETERS									
Input Capacitance	CISS			1040		pF			
Output Capacitance	Coss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V,		420		pF			
Reverse Transfer Capacitance	C <sub>RSS</sub>	f=1.0MHz		150		pF			
SWITCHING PARAMETERS									
Turn-ON Delay Time (Note 2)	t <sub>D(ON)</sub>			19	26	ns			
Turn-ON Rise Time	t <sub>R</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A,		9	13	ns			
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	V <sub>GEN</sub> =-10V, R <sub>G</sub> =6Ω		74	105	ns			
Turn-OFF Fall Time	t⊨			36	50	ns			
Total Gate Charge (Note 2)	$Q_{G}$			22.5	29	nC			
Gate-Source Charge	Q <sub>GS</sub>	$V_{DS} = -15V, V_{GS} = -10V,$		2		nC			
Gate-Drain Charge	$Q_{GD}$	I <sub>D</sub> =-4.6A		6		nC			
DRAIN-SOURCE DIODE CHARACTERISTICS									
Drain-Source Diode Forward Voltage(Note 2)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-5.3A		-0.84	-1.3	V			

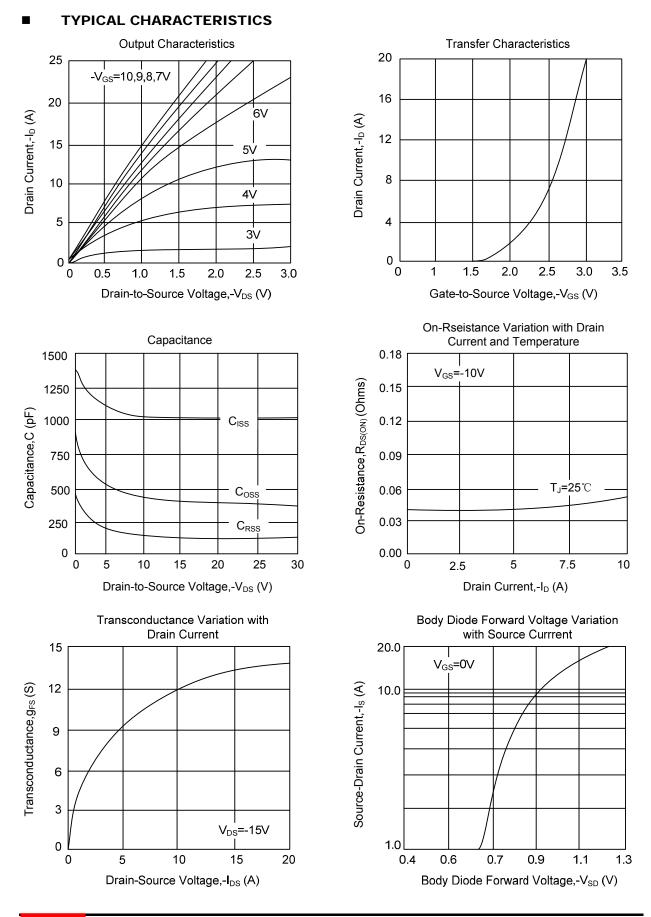
Notes: 1. Pulse width limited by  $T_{J(MAX)}$ 

2. Pulse width  $\leq$ 300us, duty cycle  $\leq$ 2%.

3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

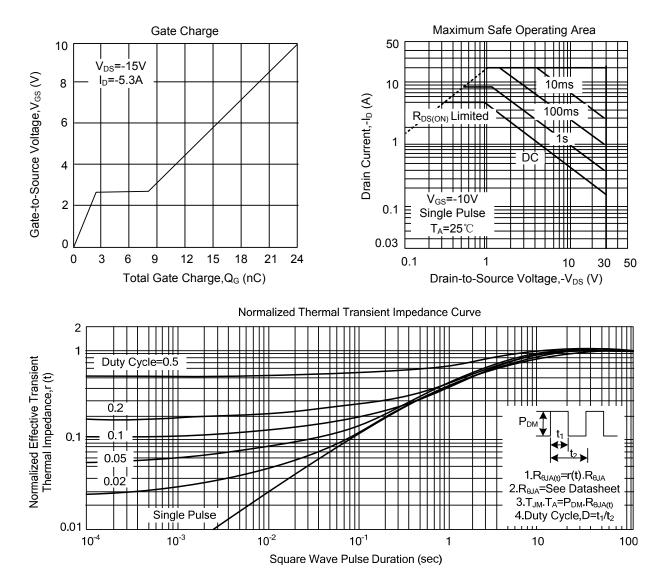


### **Power MOSFET**





### TYPICAL CHARACTERISTICS(Cont.)



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